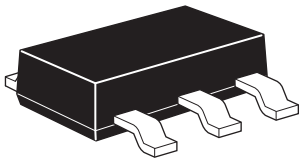
ZXMS6002G
60V N-Channel self protected enhancement mode IntelliFET™ MOSFET with status indication

Summary



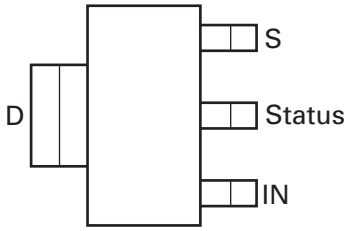
Continuous drain source voltage	**V_{DS} = 60V**
On-state resistance	**500mΩ**
Nominal load current (V_{IN} = 5V)	**1.4A**
Clamping energy	**550mJ**

Description

Self protected low side MOSFET. Monolithic over temperature, over current, over voltage (active clamp) and ESD protected logic level functionality. Intended as a general purpose switch, with status indication.

Features

- Status pin (analog status indication)
- Short circuit protection with auto restart
- Over voltage protection (active clamp)
- Thermal shutdown with auto restart
- Over-current protection
- Input protection (ESD)
- Load dump protection (actively protects load)
- Logic level input
- High continuous current rating



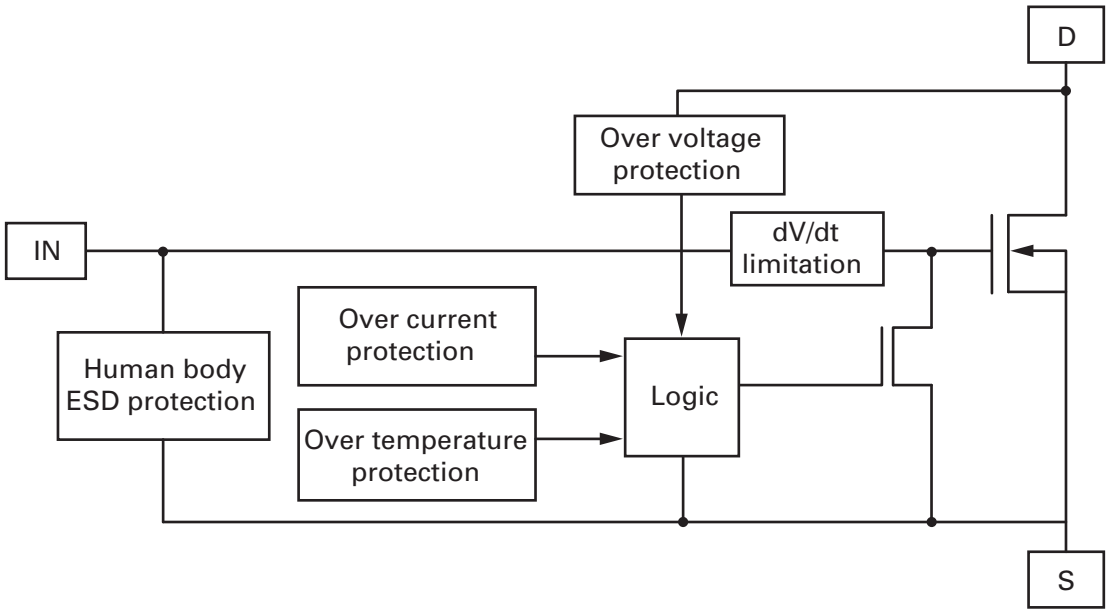
Top view

Note: The tab is connected to the drain pin and must be electrically isolated from the source pin. Connection of significant copper to the tab is recommended for best thermal performance.

Ordering information

Device	Part mark	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMS6002GTA	ZXMS6002	7	12 embossed	1000

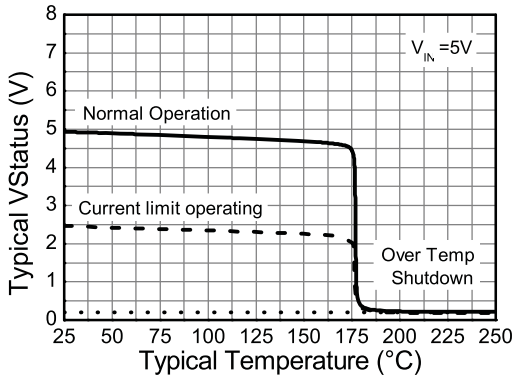
Functional block diagram



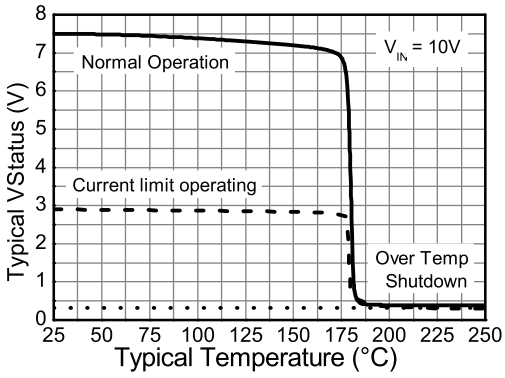
Applications and information

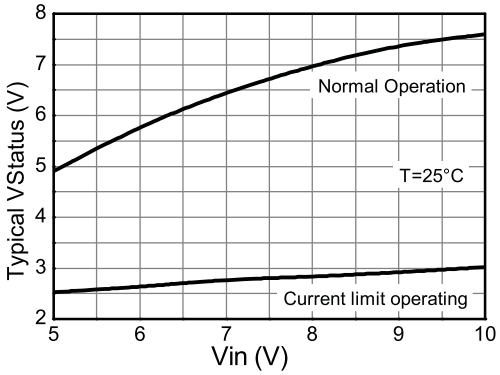
- Especially suited for loads with a high in-rush current such as lamps and motors
- All types of resistive, inductive and capacitive loads in switching applications
- μC compatible power switch for 12V and 24V DC applications
- Automotive rated
- Replaces electromechanical relays and discrete circuits
- Linear mode capability - the current-limiting protection circuitry is designed to de-activate at low V_{DS}, in order not to compromise the load current during normal operation. The design max. DC operating current is therefore determined by the thermal capability of the package/ board combination, rather than by the protection circuitry
  Note: This does not compromise the product's ability to self-protect during short-circuit load conditions.
- Status pin voltage reflects the gate drive being applied internally to the power MOSFET.
  With V_{IN} = 5V:
  Status voltage ~ 5V indicates normal operation.
  Status voltage ~ (2-3)V indicates that the device is in current-limiting mode.
  Status voltage < 1V indicates that the device is in thermal shutdown.

Current Limiting and Over Temp Shutdown Status Indication at Vin=5V



Current Limiting and Over Temp Shutdown Status Indication at Vin=10V





VStatus vs Vin

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Continuous drain-source voltage	V_{DS}	60	V
Drain-source voltage for short circuit protection V_{IN}=5V	$V_{DS(SC)}$	36	V
Drain-source voltage for short circuit protection V_{IN}=10V	$V_{DS(SC)}$	20	V
Continuous input voltage	V_{IN}	-0.2 ... +10	V
Peak input voltage	V_{IN}	-0.2 ... +20	V
Operating temperature range	T_j,	-40 to +150	°C
Storage temperature range	T_{stg}	-55 to +150	°C
Power dissipation @ T_{amb} =25°C(a)	P_D	2.5	W
Continuous drain current @ V_{IN}=10V; T_{amb}=25°C(a)	I_D	1.6	A
Continuous drain current @ V_{IN}=5V; T_{amb}=25°C(a)	I_D	1.4	A
Continuous source current (body diode)(a)	I_S	3	A
Pulsed source current (body diode)(b)	I_S	4.7	A
Unclamped single pulse inductive energy	E_{AS}	550	mJ
Load dump protection	$V_{LoadDump}$	80	V
Electrostatic discharge (human body model)	V_{ESD}	4000	V
DIN humidity category, DIN 40 040		E	
IEC climatic category, DIN IEC 68-1		40/150/56	

Thermal resistance

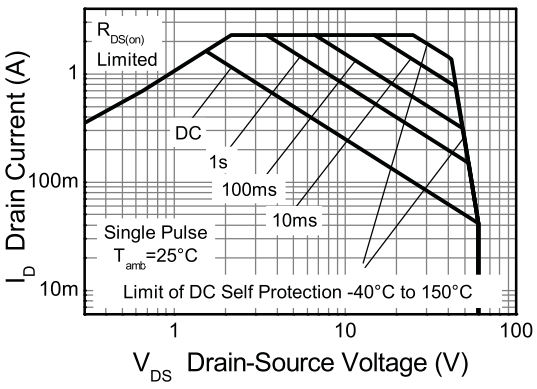
Parameter	Symbol	Limit	Unit
Junction to ambient(a)	$R_{\Theta JA}$	50	°C/W
Junction to ambient(b)	$R_{\Theta JA}$	28	°C/W

NOTES:

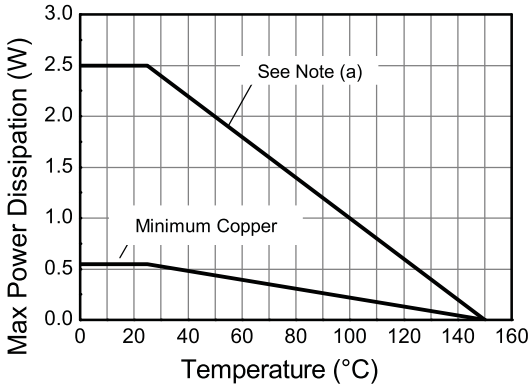
(a) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 board with a high coverage of single sided 2oz weight copper.

(b) For a device surface mounted on FR4 board as (a) and measured at t<=10s.

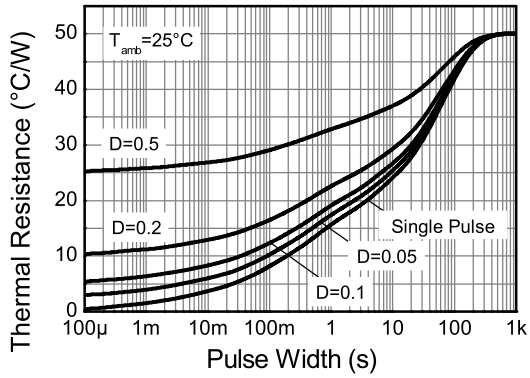
Characteristics



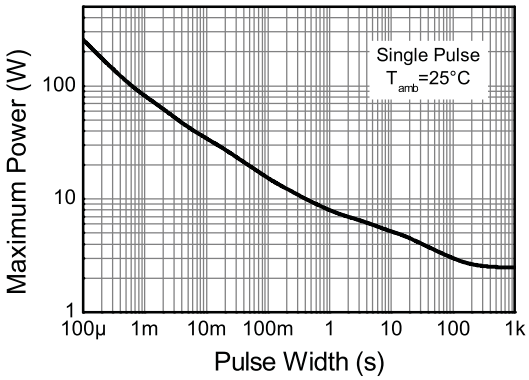
Safe Operating Area



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

Electrical characteristics (at T_{amb} = 25°C unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static characteristics						
Drain-source clamp voltage	$V_{DS(AZ)}$	60	70	75	V	I_D=10mA
Off state drain current	I_{DSS}		0.1	3	μA	V_{DS}=12V, V_{IN}=0V
Off state drain current	I_{DSS}		3	15	μA	V_{DS}=32V, V_{IN}=0V
Input threshold voltage (*)	$V_{IN(th)}$	1	2.1		V	V_{DS}=V_{GS}, I_D=1mA
Input current	I_{IN}		0.7	1.2	mA	V_{IN}=+5V
Input current	I_{IN}		1.5	2.7	mA	V_{IN}=+7V
Input current	I_{IN}		4	7	mA	V_{IN}=+10V
Static drain-source on-state resistance	$R_{DS(on)}$		520	675	mΩ	V_{IN}=5V, I_D=0.7A
Static drain-source on-state resistance	$R_{DS(on)}$		385	500	mΩ	V_{IN}=10V, I_D=0.7A
Current limit (†)	$I_{D(LIM)}$	0.7	1.0	1.5	A	V_{IN}=5V, V_{DS}>5V
Current limit(†)	$I_{D(LIM)}$	1.0	1.8	2.3	A	V_{IN}=10V, V_{DS}>5V
Dynamic characteristics						
Turn-off time (V_{IN} to 90% I_D)	t_{off}		13	20	μs	R_L=22Ω, V_{IN}=10V to 0V, V_{DD}=12V
Slew rate on (70 to 50% V_{DD})	$-dV_{DS}/dt_{on}$		8	20	V/μs	R_L=22Ω, V_{IN}=0 to 10V, V_{DD}=12V
Slew rate off (50 to 70% V_{DD})	DV_{DS}/dt_{on}		3.2	10	V/μs	R_L=22Ω, V_{IN}=10V to 0V, V_{DD}=12V
Protection functions (‡)						
Required input voltage for over temperature protection	V_{PROT}	4.5			V	
Thermal overload trip temperature	T_{JT}	150	175		°C	
Thermal hysteresis			1		°C	
Unclamped single pulse inductive energy T_j=25°C	E_{AS}	550			mJ	$I_{D(ISO)}$=0.7A, V_{DD}=32V
Unclamped single pulse inductive energy T_j=150°C	E_{AS}	200			mJ	$I_{D(ISO)}$=0.7A, V_{DD}=32V

Electrical characteristics (at T_{amb} = 25°C unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Status flag						
Normal operation	V_{STATUS}		4.95		V	V_{IN} = 5V
Current limit operating	V_{STATUS}		2.5		V	V_{IN} = 5V
Thermal shutdown activated	V_{STATUS}		0.2	1	V	V_{IN} = 5V
Normal operation	V_{STATUS}		8.0		V	V_{IN} = 10V
Current limit operation	V_{STATUS}		3.0		V	V_{IN} = 10V
Thermal shutdown activated	V_{STATUS}		0.35	1	V	V_{IN} = 10V
Inverse diode						
Source drain voltage	V_{SD}			1	V	V_{IN}=0V, $-I_D$=1.4A,

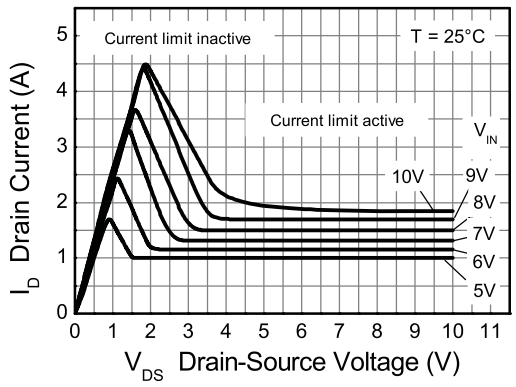
NOTES:

(*) Protection features may operate outside spec for V_{IN}<4.5V.

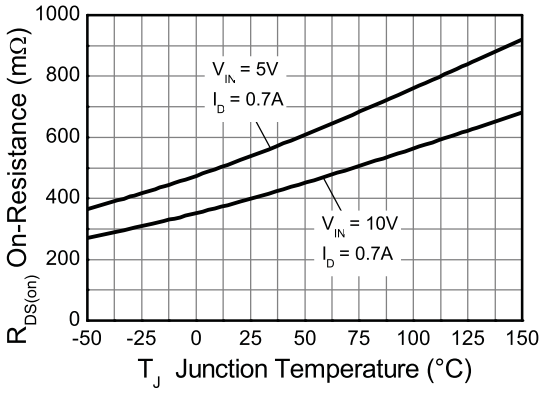
(†) The drain current is limited to a reduced value when Vds exceeds a safe level

(‡) Integrated protection functions are designed to prevent IC destruction under fault conditions described in the datasheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous, repetitive operation.

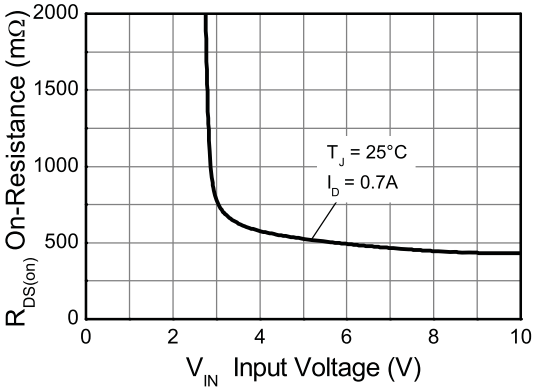
Typical characteristics



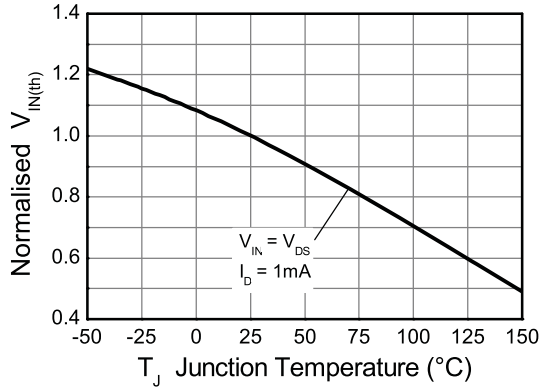
Typical Output Characteristic



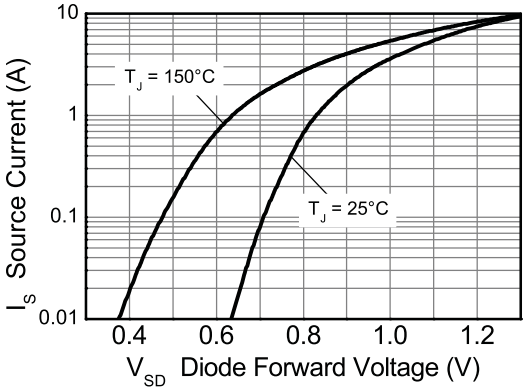
On-state Resistance vs Temperature



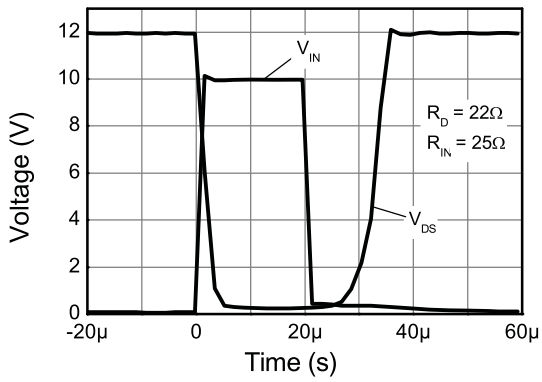
On-Resistance vs Input Voltage



Threshold Voltage vs Temperature

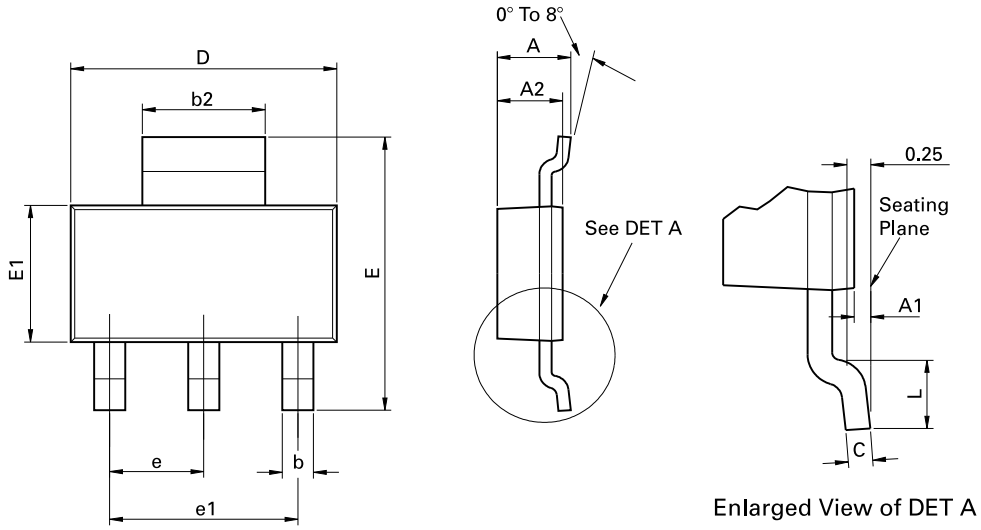


Source-Drain Diode Forward Voltage



Switching Speed

Package outline - SOT223



Conforms to JEDEC TO-261 AA Issue B

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	-	1.80	-	0.071	e	2.30 BSC		0.0905 BSC	
A1	0.02	0.10	0.0008	0.004	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
C	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-
D	6.30	6.70	0.248	0.264	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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